

# Cascadable Silicon Bipolar MMIC Amplifier

## Technical Data

#### **MSA-0770**

#### **Features**

- Cascadable 50  $\Omega$  Gain Block
- Low Operating Voltage:  $4.0\,\mathrm{V}$  Typical  $V_\mathrm{d}$
- 3 dB Bandwidth: DC to 2.5 GHz
- 13.0 dB Typical Gain at 1.0 GHz
- Unconditionally Stable (k>1)
- Hermetic, Gold-ceramic Microstrip Package

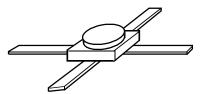
#### **Description**

The MSA-0770 is a high performance silicon bipolar Monolithic Microwave Integrated Circuit (MMIC) housed in a hermetic,

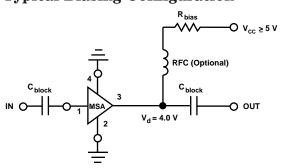
high reliability package. This MMIC is designed for use as a general purpose  $50~\Omega$  gain block. Typical applications include narrow and broad band IF and RF amplifiers in industrial and military applications.

The MSA-series is fabricated using HP's 10 GHz f<sub>T</sub>, 25 GHz f<sub>MAX</sub>, silicon bipolar MMIC process which uses nitride self-alignment, ion implantation, and gold metallization to achieve excellent performance, uniformity and reliability. The use of an external bias resistor for temperature and current stability also allows bias flexibility.

### 70 mil Package



#### **Typical Biasing Configuration**



5965-9592E 6-398

MSA-0770 Absolute Maximum Ratings

Parameter	Absolute Maximum <sup>[1]</sup>				
Device Current	60 mA				
Power Dissipation <sup>[2,3]</sup>	275 mW				
RF Input Power	+13dBm				
Junction Temperature	200°C				
Storage Temperature	−65 to 200°C				

Thermal Resistance $^{[2,4]}$ :						
$\theta_{\rm jc} = 130$ °C/W						

#### Notes

- 1. Permanent damage may occur if any of these limits are exceeded.
- 2.  $T_{CASE} = 25$ °C.
- 3. Derate at 7.7 mW/°C for  $T_C > 164$ °C.
- 4. The small spot size of this technique results in a higher, though more accurate determination of  $\theta_{jc}$  than do alternate methods. See MEASUREMENTS section "Thermal Resistance" for more information.

## Electrical Specifications<sup>[1]</sup>, $T_A = 25^{\circ}C$

Symbol	Parameters and Test Conditions:	Units	Min.	Тур.	Max.	
$G_P$	Power Gain $( S_{21} ^2)$	f = 0.1  GHz	dB	12.5	13.5	14.5
$\Delta G_{ m P}$	Gain Flatness	f = 0.1  to  1.5  GHz	dB		± 0.6	± 1.0
$f_{3dB}$	3 dB Bandwidth		GHz		2.5	
VSWR	Input VSWR	f = 0.1  to  2.5  GHz			2.0:1	
VSWK	Output VSWR	f = 0.1  to  2.5  GHz			1.6:1	
NF	$50\Omega$ Noise Figure	f = 1.0  GHz	dB		4.5	
$P_{1 dB}$	Output Power at 1 dB Gain Compression	f = 1.0  GHz	dBm		5.5	
IP <sub>3</sub>	Third Order Intercept Point	f = 1.0 GHz	dBm		19.0	
$t_{\mathrm{D}}$	Group Delay	f = 1.0  GHz	psec		130	
$V_{d}$	Device Voltage		V	3.6	4.0	4.4
dV/dT	Device Voltage Temperature Coefficient		mV/°C		-7.0	

#### Note:

1. The recommended operating current range for this device is 15 to 40 mA. Typical performance as a function of current is on the following page.

MSA-0770 Typical Scattering Parameters (Z  $_{O}$  = 50  $\Omega,$   $T_{A}$  = 25  $^{\circ}C,$   $I_{d}$  = 22 mA)

Freq.	S <sub>11</sub>		$\mathbf{S}_{21}$		S <sub>12</sub>			$\mathbf{S}_{22}$		
GHz	Mag	Ang	dB	Mag	Ang	dB	Mag	Ang	Mag	Ang
0.1	.04	-7	13.5	4.74	175	-18.6	.118	2	.20	-10
0.2	.05	-11	13.5	4.72	170	-18.4	.120	2	.19	-18
0.4	.06	<b>-</b> 24	13.4	4.70	160	-18.4	.121	6	.20	-34
0.6	.08	-38	13.4	4.65	151	-18.1	.124	7	.21	-50
0.8	.10	<b>-4</b> 8	13.2	4.58	141	-17.8	.133	9	.23	-76
1.0	.12	-58	13.0	4.47	131	-17.5	.133	9	.23	-76
1.5	.20	<b>-</b> 82	12.3	4.12	107	-16.6	.148	10	.23	-101
2.0	.30	-107	11.6	3.82	85	-15.7	.163	8	.22	-116
2.5	.37	-123	10.4	3.33	70	-15.3	.171	7	.19	-116
3.0	.42	<b>-140</b>	9.0	2.83	52	-15.4	.170	3	.20	-111
3.5	.46	-154	7.7	2.42	37	-15.4	.170	1	.23	-107
4.0	.47	-167	6.4	2.08	23	-15.5	.169	<del>-4</del>	.29	-107
5.0	.47	163	4.2	1.63	<b>-</b> 1	-15.5	.167	<b>-</b> 9	.35	-116
6.0	.51	131	2.3	1.30	<b>-</b> 23	-15.9	.160	-11	.38	-133

A model for this device is available in the DEVICE MODELS section.

## Typical Performance, $T_A = 25^{\circ}C$

(unless otherwise noted)

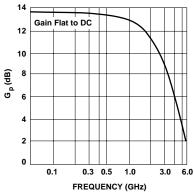


Figure 1. Typical Power Gain vs. Frequency,  $I_d = 22 \text{ mA}$ .

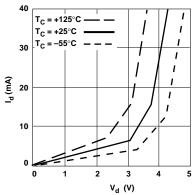


Figure 2. Device Current vs. Voltage.

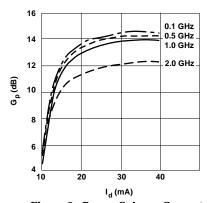


Figure 3. Power Gain vs. Current.

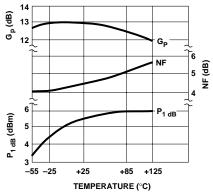


Figure 4. Output Power at 1 dB Gain Compression, NF and Power Gain vs. Case Temperature,  $f=1.0~\mathrm{GHz}$ ,  $I_d=22\mathrm{mA}$ .

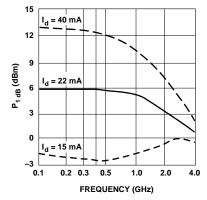


Figure 5. Output Power at 1 dB Gain Compression vs. Frequency.

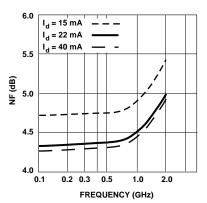


Figure 6. Noise Figure vs. Frequency.

## 70 mil Package Dimensions

